

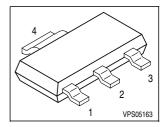


Features

- Logic Level Input
- Input Protection (ESD)
- Thermal shutdown
- Green product (RoHS compliant)
- Overload protection
- Short circuit protection
- Overvoltage protection
- Current limitation
- Analog driving possible

Product Summary

Drain source voltage	V _{DS}	42	V
On-state resistance	R _{DS(on)}	50	mΩ
Nominal load current	I _{D(Nom)}	3	А
Clamping energy	E _{AS}	500	mJ

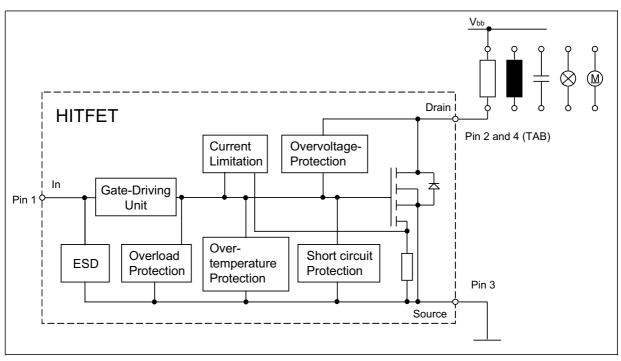


Application

- All kinds of resistive, inductive and capacitive loads in switching or linear applications
- μ C compatible power switch for 12 V DC applications
- Replaces electromechanical relays and discrete circuits

General Description

N channel vertical power FET in Smart SIPMOS[®] technology. Fully protected by embedded protection functions.





Parameter	Symbol	Value	Unit
Drain source voltage	V _{DS}	42	V
Drain source voltage for short circuit protection	V _{DS(SC)}	30	
<i>T</i> _j = -40150°C			
Continuous input current	/ _{IN}		mA
$-0.2V \le V_{\rm IN} \le 10V$		no limit	
$V_{\rm IN}$ < -0.2V or $V_{\rm IN}$ > 10V		<i>I</i> _{IN} ≤ 2	
Operating temperature	Tj	-40+150	°C
Storage temperature	T _{stg}	-55 +150	
Power dissipation	P _{tot}	3.8	W
<i>T</i> _C = 85 °C			
Unclamped single pulse inductive energy ¹⁾	E _{AS}	500	mJ
Load dump protection $V_{\text{LoadDump}}^{2)} = V_{\text{A}} + V_{\text{S}}$	V _{LD}	53.5	V
$V_{\rm IN}$ = 0 and 10 V, t _d = 400 ms, $R_{\rm I}$ = 2 Ω ,			
R _L = 4.5 Ω, V _A = 13.5 V			
Electrostatic discharge voltage (Human Body Model) V _{ESD}	2	kV
according to MIL STD 883D, method 3015.7 and			
EOS/ESD assn. standard S5.1 - 1993			

Maximum Ratings at T_i = 25°C, unless otherwise specified

Thermal resistance

junction - ambient:	R _{thJA}		K/W
@ min. footprint		125	
@ 6 cm ² cooling area $^{3)}$		72	
junction-soldering point:	R _{thJS}	17	K/W

¹ Not tested, specified by design.

 $^{2}V_{\text{Loaddump}}$ is setup without the DUT connected to the generator per ISO 7637-1 and DIN 40839

³ Device on 50mm*50mm*1.5mm epoxy PCB FR4 with 6cm² (one layer, 70µm thick) copper area for drain connection. PCB mounted vertical without blown air.



Electrical Characteristics

Parameter	Symbol		Values		Unit
at $T_{j} = 25^{\circ}$ C, unless otherwise specified		min.	typ.	max.	
Characteristics					
Drain source clamp voltage	V _{DS(AZ)}	42	-	55	V
<i>T</i> _j = - 40+ 150, <i>I</i> _D = 10 mA					
Off-state drain current $T_j = -40 \dots +150^{\circ}C$	I _{DSS}	-	1.5	10	μA
$V_{\rm DS} = 32 \text{ V}, V_{\rm IN} = 0 \text{ V}$					
Input threshold voltage	V _{IN(th)}				V
<i>I</i> _D = 1.4 mA, <i>T</i> _j = 25 °C		1.3	1.7	2.2	
$I_{\rm D}$ = 1.4 mA, $T_{\rm j}$ = 150 °C		0.8	-	-	
On state input current	I _{IN(on)}	-	10	30	μA
On-state resistance	R _{DS(on)}				mΩ
$V_{\rm IN}$ = 5 V, $I_{\rm D}$ = 3 A, $T_{\rm j}$ = 25 °C		-	45	60	
$V_{\rm IN} = 5 \text{ V}, I_{\rm D} = 3 \text{ A}, T_{\rm j} = 150 \text{ °C}$		-	75	100	
On-state resistance	R _{DS(on)}				
$V_{\rm IN}$ = 10 V, $I_{\rm D}$ = 3 A, $T_{\rm j}$ = 25 °C		-	35	50	
V _{IN} = 10 V, <i>I</i> _D = 3 A, <i>T</i> _j = 150 °C		-	65	90	
Nominal load current	I _{D(Nom)}				A
V_{DS} = 0.5 V, T_{j} < 150°C, V_{IN} = 10 V, T_{A} = 85 °C		3	-	-	
Current limit (active if V_{DS} >2.5 V) ¹)	I _{D(lim)}	18	24	30]
$V_{\rm IN}$ = 10 V, $V_{\rm DS}$ = 12 V, $t_{\rm m}$ = 200 µs					

¹Device switched on into existing short circuit (see diagram Determination of $I_{D(lim)}$). If the device is in on condit and a short circuit occurs, these values might be exceeded for max. 50 µs.



Electrical Characteristics

Parameter	Symbol		Values		Unit
at $T_{j} = 25^{\circ}$ C, unless otherwise specified		min.	typ.	max.	

Dynamic Characteristics

Turn-on time $V_{\rm IN}$ to 90% $I_{\rm D}$:	t _{on}	-	60	100	μs
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V					
Turn-off time $V_{\rm IN}$ to 10% $I_{\rm D}$:	t _{off}	-	60	100	
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V					
Slew rate on 70 to 50% V _{bb} :	-dV _{DS} /dt _{on}	-	0.3	1.5	V/µs
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 0 to 10 V, $V_{\rm bb}$ = 12 V					
Slew rate off 50 to 70% V _{bb} :	dV _{DS} /dt _{off}	-	0.7	1.5	
$R_{\rm L}$ = 4.7 Ω , $V_{\rm IN}$ = 10 to 0 V, $V_{\rm bb}$ = 12 V					

Protection Functions¹⁾

Thermal overload trip temperature	T _{it}	150	175	-	°C
Input current protection mode	I _{IN(Prot)}	80	160	300	μA
Input current protection mode	I _{IN(Prot)}	-	130	300	
<i>T</i> _j = 150 °C					
Unclamped single pulse inductive energy ²⁾	E _{AS}	500	-	-	mJ
$I_{\rm D}$ = 3 A, $T_{\rm j}$ = 25 °C, $V_{\rm bb}$ = 12 V					

Inverse Diode

Inverse diode forward voltage	V _{SD}	-	1	-	V
<i>I</i> _F = 15 A, <i>t</i> _m = 250 μs, <i>V</i> _{IN} = 0 V,					
<i>t</i> _P = 300 μs					

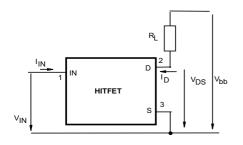
¹Integrated protection functions are designed to prevent IC destruction under fault conditions described in the data sheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous repetitive operation.

² Not tested, specified by design.

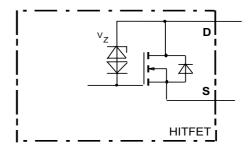


Block diagram

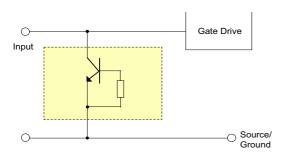
Terms



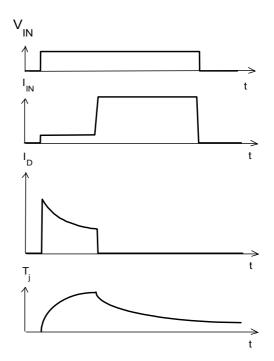
Inductive and overvoltage output clamp



Input circuit (ESD protection)



Short circuit behaviour

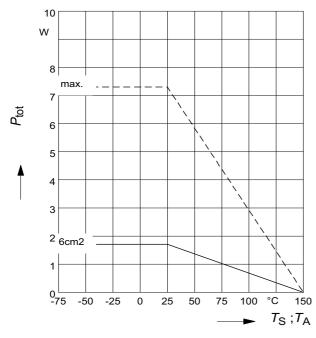




1 Maximum allowable power dissipation

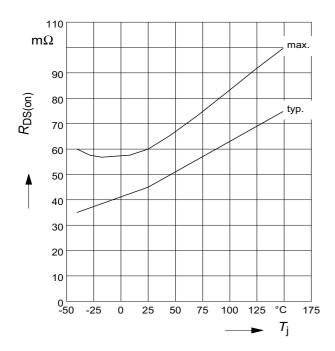
P_{tot} = f(T_S) resp.

 $P_{tot} = f(T_A) @ R_{thJA}=72 \text{ K/W}$



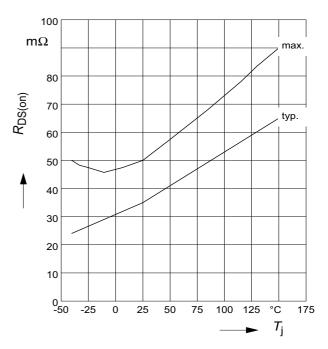
3 On-state resistance

R_{ON} = f(T_j); I_D= 3A; V_{IN}=5V

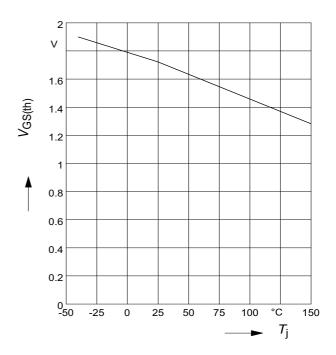


2 On-state resistance

 $R_{ON} = f(T_j); I_D = 3A; V_{IN} = 10V$



4 Typ. input threshold voltage V_{IN(th)} = f(T_j); *I*_D = 0.7 mA; V_{DS} = 12V

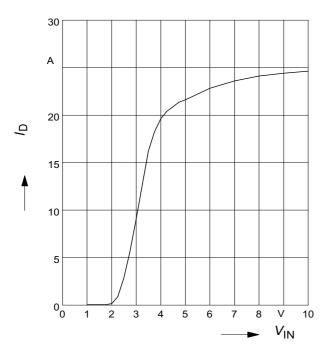


Datasheet

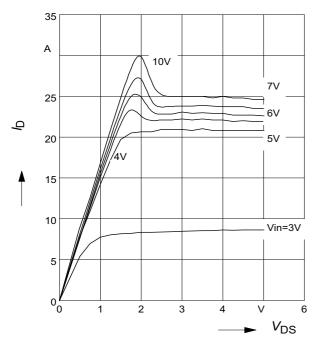


5 Typ. transfer characteristics

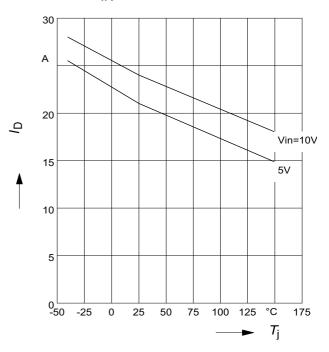
I_**=f(V**_{**I**N}); V_{DS}=12V; T_{Jstart}=25°C}



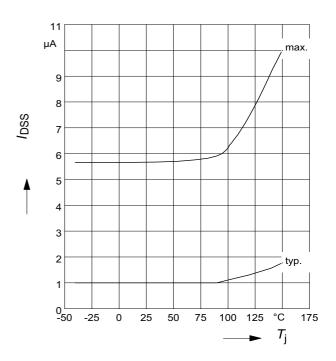
7 Typ. output characteristics I_D=f(V_{DS}); T_{Jstart}=25°C Parameter: V_{IN}



6 Typ. short circuit current I_{D(lim)} = f(Tj); V_{DS}=12V Parameter: V_{IN}



8 Typ. off-state drain current $I_{\text{DSS}} = f(T_{\text{j}})$

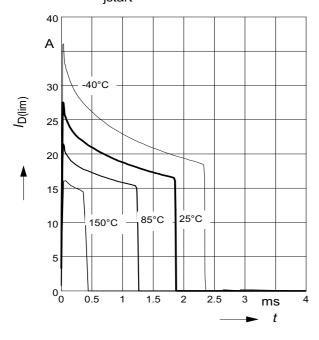


Datasheet



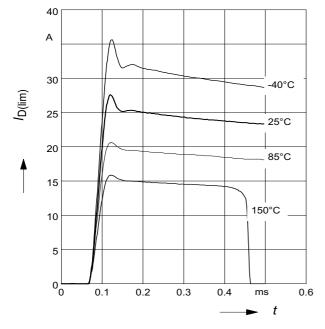
9 Typ. overload current

 $I_{D(lim)} = f(t)$, $V_{bb} = 12$ V, no heatsink Parameter: T_{jstart}

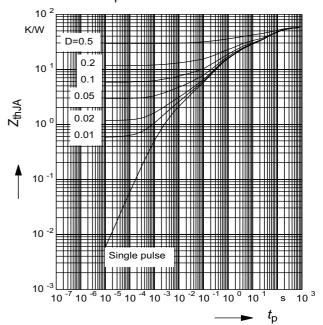


11 Determination of $l_{D(lim)}$ $l_{D(lim)} = f(t); t_m = 200 \mu s$

Parameter: T_{Jstart}



10 Typ. transient thermal impedance $Z_{thJA}=f(t_p) @ 6 cm^2$ cooling area Parameter: $D=t_p/T$



Datasheet



Package Outlines

Package Outlines 1

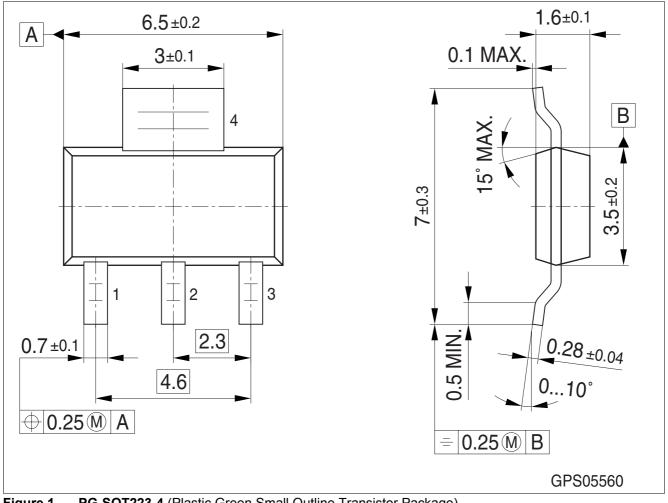


Figure 1 PG-SOT223-4 (Plastic Green Small Outline Transistor Package)

Green Product (RoHS compliant)

To meet the world-wide customer requirements for environmentally friendly products and to be compliant with government regulations the device is available as a green product. Green products are RoHS-Compliant (i.e Pbfree finish on leads and suitable for Pb-free soldering according to IPC/JEDEC J-STD-020).

Please specify the package needed (e.g. green package) when placing an order

You can find all of our packages, sorts of packing and others in our Infineon Internet Page "Products": http://www.infineon.com/products.

Datasheet

Rev. 1.3, 2008-04-14



Revision History

2 Revision History

Date	Changes
2008-04-14	Package information updated to SOT223-4
2007-03-28	released automotive green version
	Package parameter (humidity and climatic) removed in Maximum ratings
	AEC icon added
	RoHS icon added
	Green product (RoHS-compliant) added to the feature list
	Package information updated to green
	Green explanation added
2004-02-02	released production version
	2008-04-14 2007-03-28

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